# 74HC540-Q100; 74HCT540-Q100

Octal buffer/line driver; 3-state; inverting

Rev. 3 — 21 January 2013

**Product data sheet** 

### 1. General description

The 74HC540-Q100; 74HCT540-Q100 is an 8-bit inverting buffer/line driver with 3-state outputs. The device features two output enables ( $\overline{\text{OE}}1$  and  $\overline{\text{OE}}2$ ). A HIGH on  $\overline{\text{OE}}n$  causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{\text{CC}}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Inverting outputs
- Complies with JEDEC standard no. 7A
- Input levels:
  - ♦ For 74HC540-Q100: CMOS level
  - ◆ For 74HCT540-Q100: TTL level
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

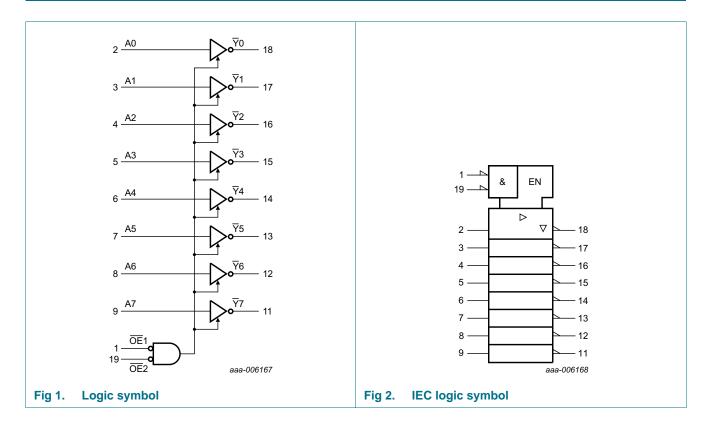
## 3. Ordering information

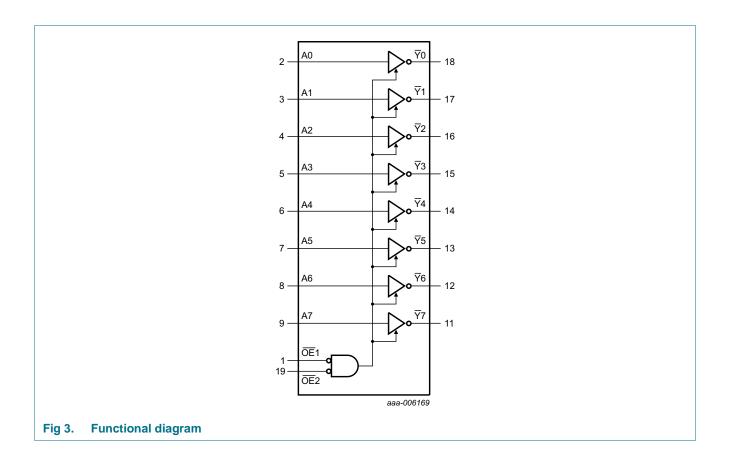
Table 1. Ordering information

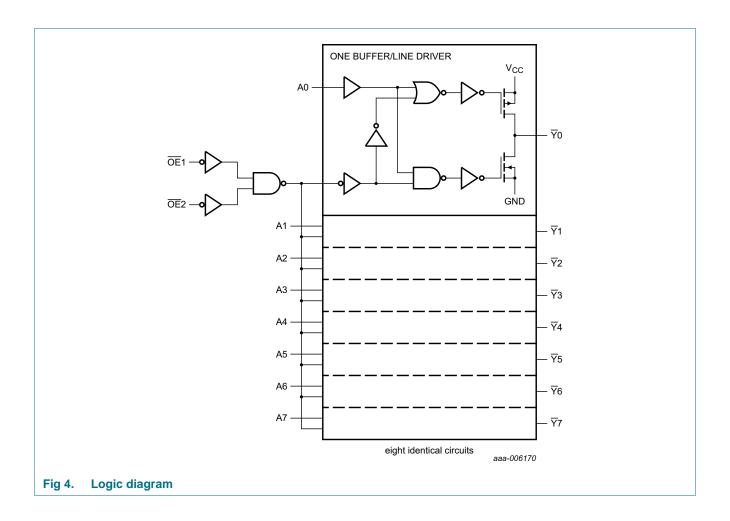
Type number	Package			
	Temperature range	Name	Description	Version
74HC540N-Q100	−40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1
74HCT540N-Q100				
74HC540D-Q100	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads;	SOT163-1
74HCT540D-Q100			body width 7.5 mm	



## 4. Functional diagram

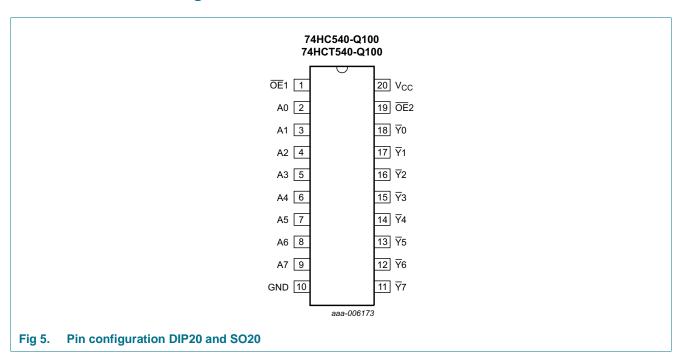






## 5. Pinning information

#### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

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Symbol	Pin	Description
OE1	1	output enable input (active LOW)
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
$\overline{Y}$ 0 to $\overline{Y}$ 7	18, 17, 16, 15, 14, 13, 12, 1	data output
OE <sub>2</sub>	19	output enable input (active LOW)
$V_{CC}$	20	supply voltage

## 6. Functional description

Table 3. Functional table[1]

Control		Input	Output
OE1	OE2	An	Yn
L	L	L	Н
L	L	Н	L
X	Н	X	Z
Н	X	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

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## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	[1] -	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	[1] -	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35	mA
I <sub>CC</sub>	supply current		-	70	mA
I <sub>GND</sub>	ground current		-70	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation		[2]		
	DIP20		-	750	mW
	SO20		-	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Parameter	Conditions	74HC5	40-Q100	1	74НСТ	Unit		
		Min	Тур	Max	Min	Тур	Max	
supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
ambient temperature		-40	+25	+125	-40	+25	+125	°C
input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
	$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V
	supply voltage input voltage output voltage ambient temperature	supply voltage input voltage output voltage ambient temperature input transition rise and fall rate $ \frac{V_{CC} = 2.0 \text{ V}}{V_{CC} = 4.5 \text{ V}} $		$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		

<sup>[2]</sup> For DIP20 packages: above 70 °C the value of P<sub>tot</sub> derates linearly with 12 mW/K. For SO20 packages: above 70 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.

## 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Min   Max   Min	Symbol	Parameter	Conditions	Tai	<sub>mb</sub> = 25	°C		: –40 °C 85 °C	T <sub>amb</sub> = to +	Uni	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $				Min	Тур	Max	Min	Max	Min	Max	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	74HC54	0-Q100					1			1	'
V <sub>CC</sub> = 6.0 V   V <sub>CC</sub> = 0.0	$V_{IH}$		V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		input voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
Voc   6.0 V   -2.8   1.8   -3	V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	8.0	0.5	-	0.5	-	0.5	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		input voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $			$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V <sub>OH</sub>		$V_I = V_{IH}$ or $V_{IL}$								
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
$V_{OL} = \begin{array}{c} I_{O} = -6.0 \text{ m/s}; \ V_{CC} = 4.5 \text{ V} & 3.98 & 4.32 & - & 3.84 & - & 3.7 & - \\ I_{O} = -7.8 \text{ m/s}; \ V_{CC} = 6.0 \text{ V} & 5.48 & 5.81 & - & 5.34 & - & 5.2 & - \\ \hline V_{OL} = \begin{array}{c} LOW\text{-level} \\ \text{Output voltage} \end{array} & \begin{array}{c} V_{I} = V_{IH} \text{ or } V_{IL} \\ I_{O} = 20 \ \mu\text{A}; \ V_{CC} = 2.0 \text{ V} & - & 0 & 0.1 & - & 0.1 & - & 0.1 \\ I_{O} = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \text{ V} & - & 0 & 0.1 & - & 0.1 & - & 0.1 \\ I_{O} = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \text{ V} & - & 0 & 0.1 & - & 0.1 & - & 0.1 \\ I_{O} = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \text{ V} & - & 0.15 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 6.0 \ \text{m/s}; \ V_{CC} = 4.5 \text{ V} & - & 0.16 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 7.8 \ \text{m/s}; \ V_{CC} = 6.0 \text{ V} & - & 0.16 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 7.8 \ \text{m/s}; \ V_{CC} = 6.0 \text{ V} & - & 0.16 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 0.78 \ \text{m/s}; \ V_{CC} = 6.0 \text{ V} & - & 0.16 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 0.78 \ \text{m/s}; \ V_{CC} = 6.0 \text{ V} & - & 0.16 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 0.78 \ \text{m/s}; \ V_{CC} = 6.0 \text{ V} & - & 0.16 & 0.26 & - & 0.33 & - & 0.4 \\ I_{O} = 0.0 \ \text{m/s}; \ V_{CC} = 0.0 \ \text{N}; \ V_{CC} =$			$I_{O} = -20 \mu A$ ; $V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
$V_{OL} \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$			$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$			$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V <sub>OL</sub>		$V_I = V_{IH}$ or $V_{IL}$								
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	V
$\begin{array}{cccccccccccccccccccccccccccccccccccc$			$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
			$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	l <sub>l</sub>		$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
$V_{CC} = 6.0 \text{ V}$ $C_{I}  \text{input}  \text{capacitance}$ $74HCT540\text{-Q}100$ $V_{IH}  \text{HIGH-level}  \text{input voltage}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ $\text{input voltage}$ $V_{IL}  \text{LOW-level}  \text{input voltage}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ $\text{-}  1.2  0.8  \text{-}  0.8  \text{-}  0.8$ $\text{input voltage}$ $V_{OH}  \text{HIGH-level}  \text{output voltage}$ $V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$ $\text{output voltage}$ $V_{OH}  \text{-}  \text{-}  4.4  \text{-}  4.$	loz		$V_O = V_{CC}$ or GND; other inputs at $V_{CC}$ or GND;	-	±0.5	-	±5.0	-	±10	-	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I <sub>CC</sub>	supply current		-	-	8.0	-	80	-	160	μΑ
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Cı			-	3.5	-	-	-	-	-	pF
	74HCT5	40-Q100									
input voltage $V_{OH} \qquad \begin{array}{c} \text{Input voltage} \\ \text{V}_{OH} \\ \text{output voltage} \end{array} \qquad \begin{array}{c} V_{I} = V_{IH} \text{ or } V_{IL}; \ V_{CC} = 4.5 \ V \\ \\ I_{O} = -20 \ \mu\text{A} \\ \end{array} \qquad \begin{array}{c} 4.4 \\ 4.5 \\ \end{array} \qquad \begin{array}{c} -4.4 \\ - \end{array} \qquad \begin{array}{c} 4.4 \\ - \end{array} \qquad \begin{array}{c} -4.4 \\ - \end{array} \qquad \begin{array}{c}$	V <sub>IH</sub>		V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
output voltage $I_0 = -20 \mu A$ 4.4 4.5 - 4.4 - 4.4	$V_{IL}$		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	8.0	V
10 = -20 μΩ	V <sub>OH</sub>		$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
$I_{O} = -6.0 \text{ mA}$ 3.98 4.32 - 3.84 - 3.7 -		output voltage	$I_0 = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
			$I_{O} = -6.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T <sub>ar</sub>	<sub>nb</sub> = 25	°C		- –40 °C 85 °C		= –40 °C I25 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 20 \mu A;$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA};$	-	0.16	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l <sub>OZ</sub>	OFF-state output current	per input pin; $V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; other inputs at $V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$ ; $I_O = 0 \text{ A}$	-	-	±0.5	-	±5.0	-	±10	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μА
Δl <sub>CC</sub>	additional supply current	per input pin; $I_O = 0$ A; $V_I = V_{CC} - 2.1$ V; other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5$ V to 5.5 V								
		An input	-	140	504	-	630	-	686	μΑ
		OE1 input	-	150	540	-	675	-	735	μΑ
		OE2 input	-	100	360	-	450	-	490	μΑ
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF

## 10. Dynamic characteristics

Table 7. Dynamic characteristics

 $GND = 0 \ V; \ C_L = 50 \ pF;$  for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions		Tan	<sub>nb</sub> = 25	°C	$T_{amb} = -40^{\circ}$	Unit	
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HC540	)-Q100				•				•
t <sub>pd</sub>	propagation delay	An to Yn; see Figure 6	[1]						
		V <sub>CC</sub> = 2.0 V		-	30	100	125	150	ns
	$V_{CC} = 4.5 \text{ V}$		-	11	20	25	30	ns	
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$		-	9	17	21	26	ns
t <sub>en</sub>	enable time	OEn to Yn; see Figure 7	[1]						
		$V_{CC} = 2.0 \text{ V}$		-	52	160	200	240	ns
		V <sub>CC</sub> = 4.5 V		-	19	32	40	48	ns
		$V_{CC} = 6.0 \text{ V}$		-	15	27	34	41	ns
t <sub>dis</sub>	disable time	OEn to Yn; see Figure 7	[1]						
		V <sub>CC</sub> = 2.0 V		-	61	160	200	240	ns
		$V_{CC} = 4.5 \text{ V}$		-	22	32	40	48	ns
		V <sub>CC</sub> = 6.0 V		-	18	27	34	41	ns

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Table 7. Dynamic characteristics

 $GND = 0 \text{ V; } C_L = 50 \text{ pF; for test circuit see Figure 8.}$ 

Symbol	Parameter	Conditions		Tar	<sub>nb</sub> = 25	°C	$T_{amb} = -40^{\circ}$	C to +125 °C	Unit
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	
t <sub>t</sub>	transition time	see Figure 6	[2]	•		'	'		'
		$V_{CC} = 2.0 \text{ V}$		-	14	60	75	90	ns
		$V_{CC} = 4.5 \text{ V}$		-	5	12	15	18	ns
		$V_{CC} = 6.0 \text{ V}$		-	4	10	13	15	ns
$C_{PD}$	power dissipation capacitance	per package; V <sub>I</sub> = GND to V <sub>CC</sub>	[3]	-	39	-	-	-	pF
74HCT5	40-Q100								
t <sub>pd</sub>	propagation delay	An to Yn; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	13	24	30	36	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns
t <sub>en</sub>	enable time	OEn to Yn; see Figure 7	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	22	35	44	53	ns
t <sub>dis</sub>	disable time	OEn to Yn; see Figure 7	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	23	35	44	53	ns
t <sub>t</sub>	transition time	V <sub>CC</sub> = 4.5 V; see <u>Figure 6</u>	[2]	-	5	12	15	18	ns
$C_{PD}$	power dissipation capacitance	per package; V <sub>I</sub> = GND to V <sub>CC</sub> – 1.5 V	[3]	-	44	-	-	-	pF

<sup>[1]</sup>  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

 $t_{\text{en}}$  is the same as  $t_{\text{PZL}}$  and  $t_{\text{PZH}}.$ 

 $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ):

$$P_D$$
 =  $C_{PD} \times V_{CC}{}^2 \times f_i \times N$  +  $\sum$  ( $C_L \times V_{CC}{}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o$  = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

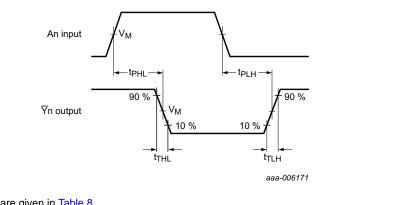
V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$ 

<sup>[2]</sup>  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

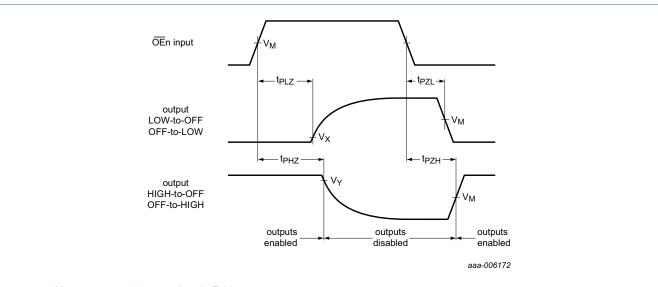
#### 11. Waveforms



Measurement points are given in Table 8.

 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

Fig 6. Input to output propagation delays



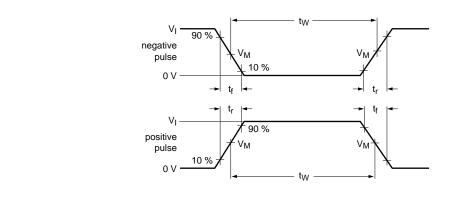
Measurement points are given in Table 8.

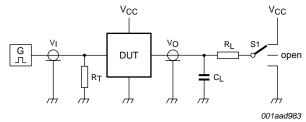
 $\ensuremath{V_{\text{OL}}}$  and  $\ensuremath{V_{\text{OH}}}$  are typical voltage output levels that occur with the output load.

Fig 7. 3-state enable and disable times

Table 8. Measurement points

Туре	Input	Output		
	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
74HC540-Q100	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	0.1V <sub>CC</sub>	0.9V <sub>CC</sub>
74HCT540-Q100	1.3 V	1.3 V	0.1V <sub>CC</sub>	0.9V <sub>CC</sub>





Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator

C<sub>L</sub> = Load capacitance including jig and probe capacitance

R<sub>L</sub> = Load resistance

S1 = Test selection switch

Fig 8. Test circuit for measuring switching times

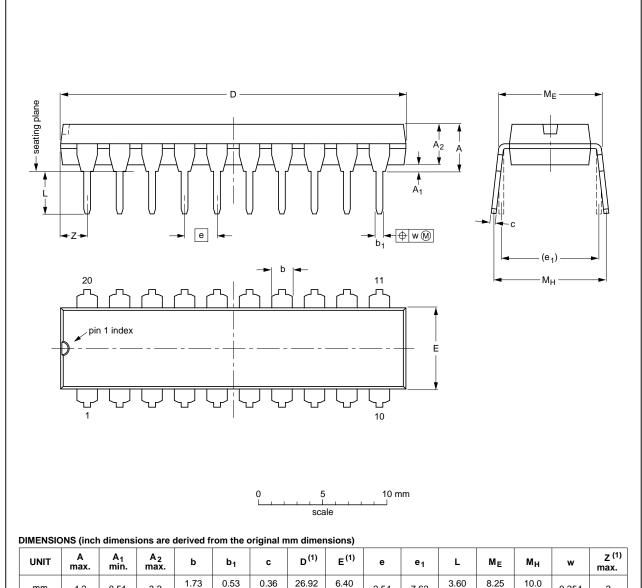
Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	R <sub>L</sub>	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
74HC540-Q100	$V_{CC}$	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	
74HCT540-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	

## 12. Package outline

#### DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1



UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	L	ME	Мн	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

#### Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

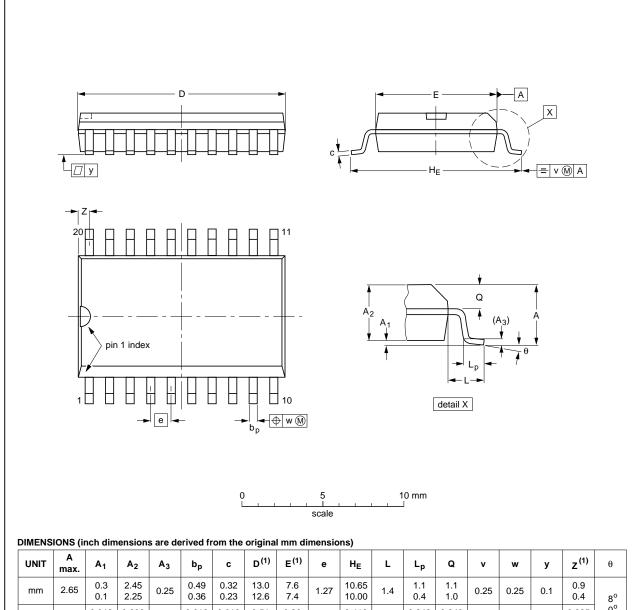
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT146-1		MS-001	SC-603			<del>99-12-27</del> 03-02-13	

Fig 9. Package outline SOT146-1 (DIP20)

74HC\_HCT540\_Q100

#### SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	C	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	٧	w	у	z <sup>(1)</sup>	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	IOOUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT163-1	075E04	MS-013				<del>99-12-27</del> 03-02-19	

Fig 10. Package outline SOT163-1 (SO20)

74HC\_HCT540\_Q100

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### 13. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MIL	Military
MM	Machine Model

## 14. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT540_Q100 v.1	20130121	Product data sheet	-	-

### 15. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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74HC\_HCT540\_Q100

## 74HC540-Q100; 74HCT540-Q100

**NXP Semiconductors** 

Octal buffer/line driver; 3-state; inverting

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Octal buffer/line driver; 3-state; inverting

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